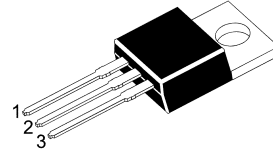


**FUKUCOM COMPANY LTD.****福 靈 有 限 公 司**FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

ST 13007**NPN Silicon Transistor**

for high-voltage, high-speed power switching .



1.Base 2.Collector 3.Emitter

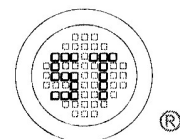
TO-220 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	700	V
Collector Emitter Voltage	V _{CEO}	400	V
Emitter Base Voltage	V _{EBO}	9	V
Collector Current	I _C	8	A
Power Dissipation	P _{tot}	80	W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _S	-55 to +150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V _{CE} = 5 V, I _C = 2 A	h _{FE}	10	-	70	-
Collector Emitter Breakdown Voltage at I _C = 10 mA	V _{(BR)CEO}	400	-	-	V
Collector Base Breakdown Voltage at I _C = 100 μA	V _{(BR)CBO}	700	-	-	V
Emitter Base Breakdown Voltage at I _E = 1 mA	V _{(BR)EBO}	9	-	-	V
Collector Cutoff Current at V _{CB} = 700 V	I _{CBO}	-	-	100	μA
Emitter Cutoff Current at V _{EB} = 9 V	I _{EBO}	-	-	100	μA
Collector Emitter Saturation Voltage at I _C = 5 A, I _B = 1 A	V _{CE(sat)}	-	-	2	V
Base Emitter Saturation Voltage at I _C = 5 A, I _B = 1 A	V _{BE(sat)}	-	-	1.6	V
Current Gain Bandwidth Product at V _{CE} = 10 V, I _C = 0.5 A	f _T	4	-	-	MHz
Output Capacitance at V _{CB} = 10 V, f = 0.1 MHz	C _{OB}	-	110	-	pF

**SEMTECH**

Dated : 22/03/2006



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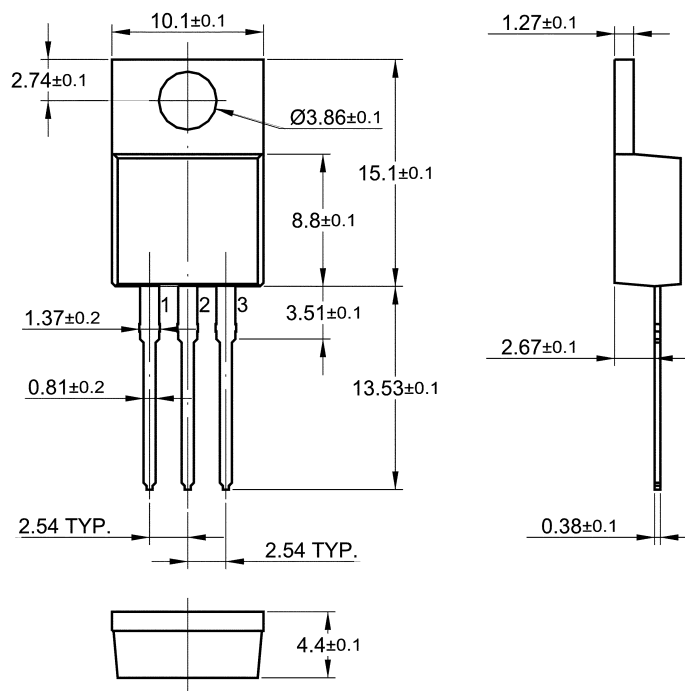
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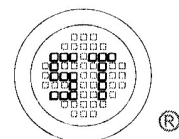
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ST 13007

TO-220 PACKAGE OUTLINE



Dimensions in mm



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